

An article entitled "Anisotropy of electrical and optical properties in B-Ga₂O₃ single crystals" from Appl. Phys. Lett. 71(7), N. Ueda et al., pp. 933-935 (Aug. 18, 1997).
 An article entitled "Synthesis and control of conductivity of ultraviolet transmitting B-Ga₂O₃ single crystals" from Appl. Phys. Lett. 70(26), N. Ueda, pp. 3561-3563 (Jun. 30, 1997).

Primary Examiner:
 Attorney, Agent or Firm:

Figures

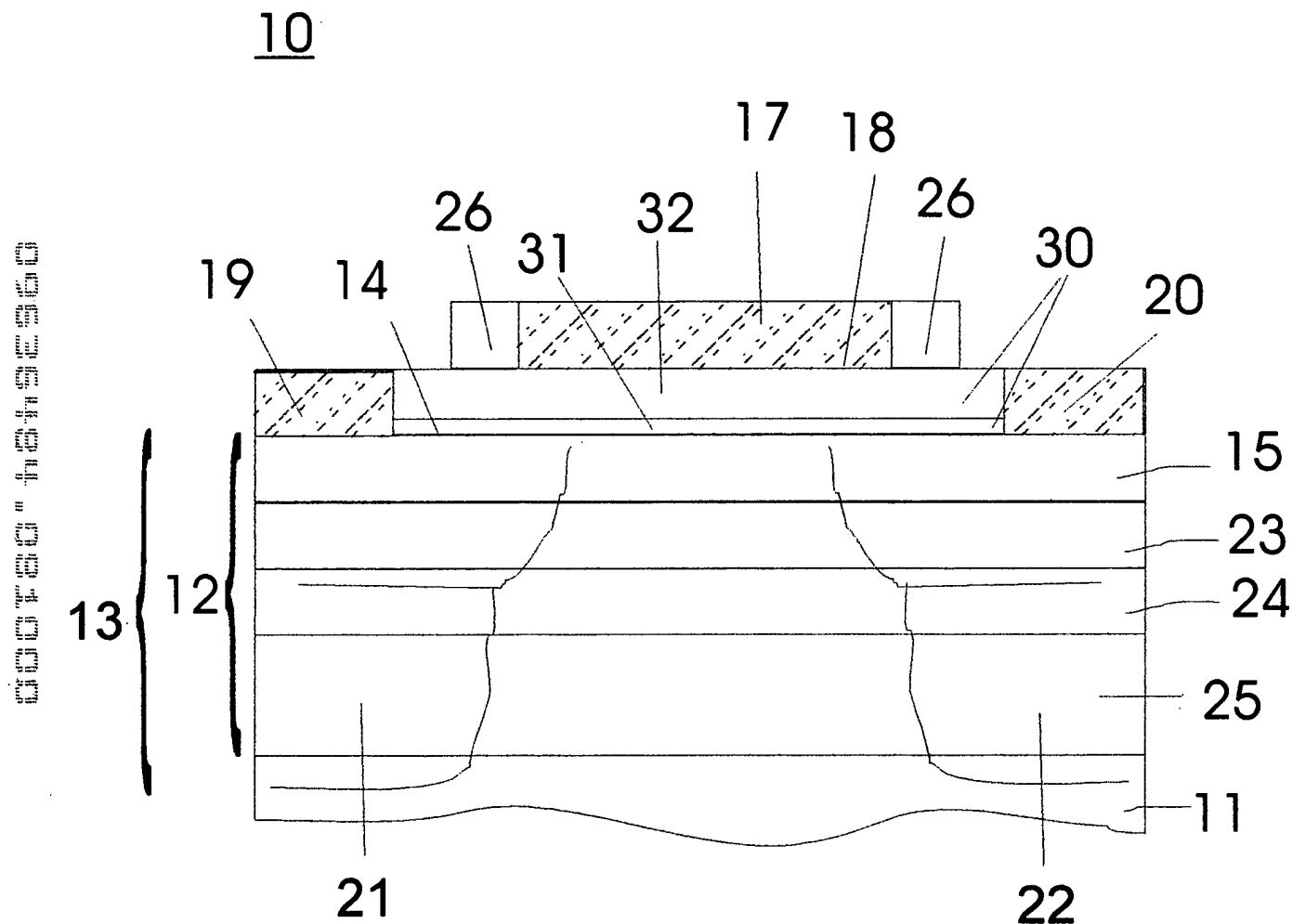


Figure 1

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graph TD; 100[Provide Compound Semiconductor Substrate] --> 102[Deposit Compound Semiconductor Epitaxial Structure]; 102 --> 103[Transfer Compound Semiconductor Structure to Insulator Deposition Chamber]; 103 --> 104[Deposit layer of Gallium Oxygen Compounds on upper Surface of Compound Semiconductor Structure]; 104 --> 105[Deposit Layer of Gallium Oxygen and at least one Rare Earth Element onto Upper Surface of Gallium Oxygen Layer]; 105 --> 106[Position Stable Refractory Metal on Gate Oxide Insulator Layer Structure]; 106 --> 108[Provide Source and Drain Implant Regions that are Self-Aligned to Gate Electrode]; 108 --> 110[Position Source and Drain Ohmic Contacts]; 110 --> 112[Provide Interconnection Means for the Formation of an Integrated Circuit];
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Provide Compound Semiconductor Substrate 100

Deposit Compound Semiconductor Epitaxial Structure 102

Transfer Compound Semiconductor Structure to Insulator Deposition Chamber 103

Deposit layer of Gallium Oxygen Compounds on upper Surface of Compound Semiconductor Structure 104

Deposit Layer of Gallium Oxygen and at least one Rare Earth Element onto Upper Surface of Gallium Oxygen Layer 105

Position Stable Refractory Metal on Gate Oxide Insulator Layer Structure 106

Provide Source and Drain Implant Regions that are Self-Aligned to Gate Electrode 108

Position Source and Drain Ohmic Contacts 110

Provide Interconnection Means for the Formation of an Integrated Circuit 112

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